



MK3400A

N-Channel 30-V(D-S) MOSFET

V(BR)DSS	RDS(on)MAX	ID
30 V	32mΩ@10V	5.8A
	35mΩ@4.5V	
	50mΩ@2.5V	

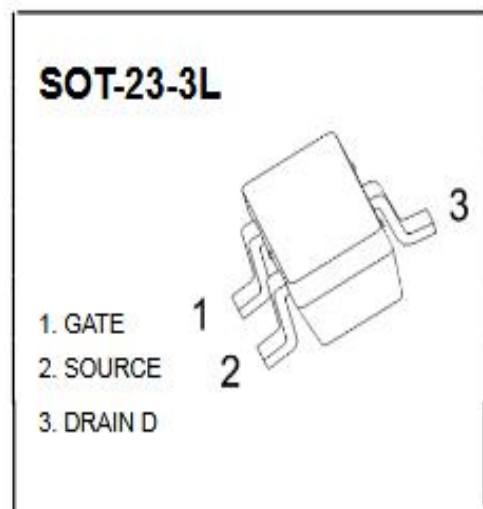
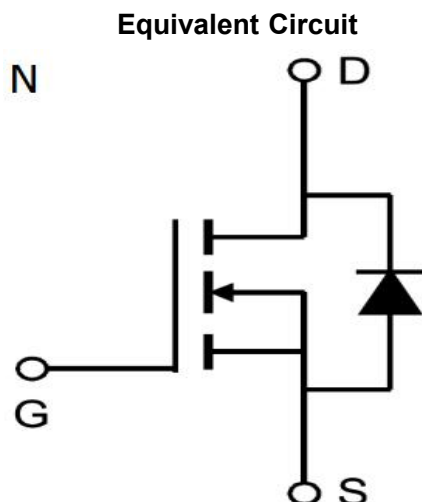
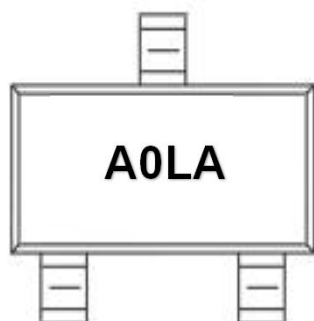
FEATURE

※ TrenchFET Power MOSFET

APPLICATION

- ※ Load Switch for Portable Devices
- ※ DC/DC Converter

MARKING



Maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	VGS	±12	
Continuous Drain Current	ID	5.8	A
Pulsed Diode Current	IDM	30	
Continuous Source-Drain Current(Diode Conduction)	IS	0.8	
Power Dissipation	PD	1.4	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	125	℃/W
Operating Junction	TJ	150	℃
Storage Temperature	TSTG	-55~+150	℃



MOSFET ELECTRICAL CHARACTERISTICS

Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)

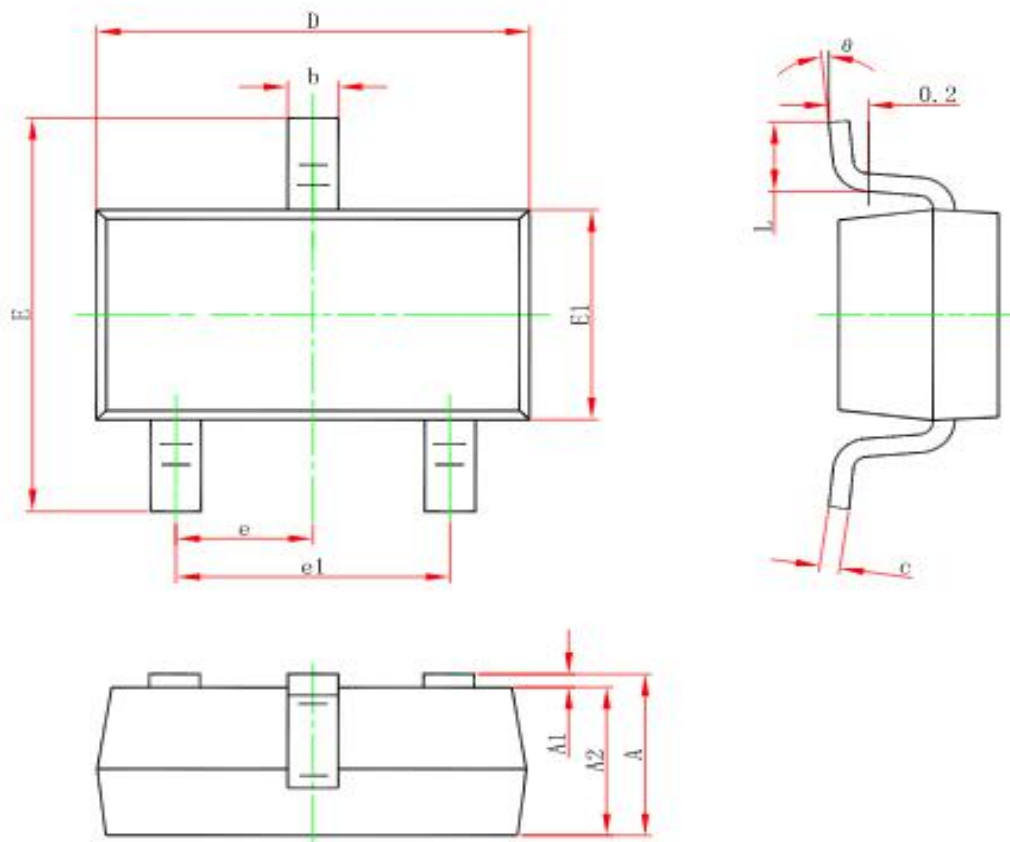
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = 250μA	30			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = 250μA	0.6		1.2	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±12V			±100	nA
Zero gate voltage drain current	IDSS	VDS = 24V, VGS =0V			1	μA
Drain-source on-state resistancea	RDS(on)	VGS = 10V, ID = 5.8A		25	32	mΩ
		VGS = 4.5V, ID = 4.8A		27	35	mΩ
		VGS = 2.5V, ID = 4.0A		39	50	mΩ
Forward transconductancea	gfs	VDS = 4.5V, ID = 5A		15		S
Diode forward voltage	VSD	IS=1A,VGS=0V		0.7	1.3	V
Dynamic						
Input capacitance	Ciss	VDS = 15V,VGS =0V, f=1MHz		823	1050	pF
Output capacitance	Coss			99		pF
Reverse transfer capacitanceb	Crss			77		pF
Total gate charge	Qg	VDS = 10V,VGS = 4.5V, ID = -5.8A		11	14	nC
Gate-source charge	Qgs			1.3		nC
Gate-drain charge	Qgd			2.8		nC
Gate resistance	Rg	f=1MHz			3.6	Ω
Switchingb						
Turn-on delay time	td(on)	VDD= 10V RL=10Ω, ID ≈ 1A, VGEN= 4.5V,Rg=6Ω		7	15	ns
Rise time	tr			15	20	ns
Turn-off delay time	td(off)			38	50	ns
Fall time	tf			3	10	ns
Drain-source body diode characteristics						
Continuous Source-Drain Diode Current	IS	Tc=25℃			1.2	A
Pulsed Diode forward Curren	ISM				20	A

Note :

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.



SOT-23-3L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°



Typical Characteristics:

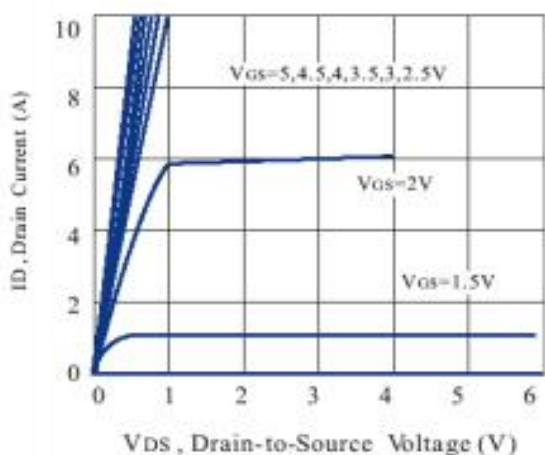


Figure 1. Output Characteristics

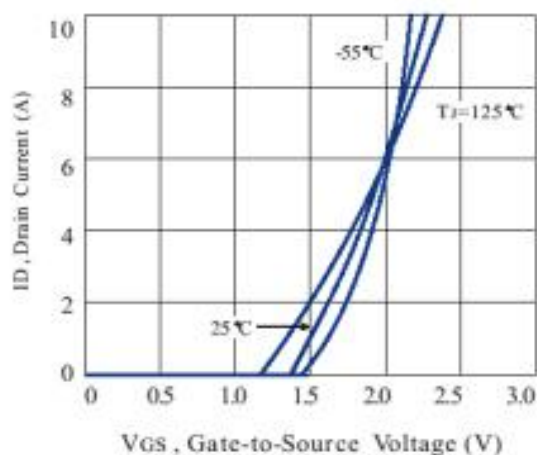


Figure 2. Transfer Characteristics

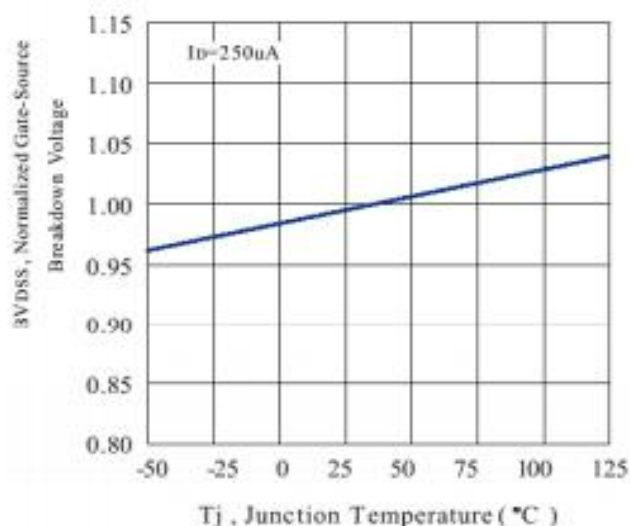


Figure 3. Breakdown Voltage Variation with Temperature

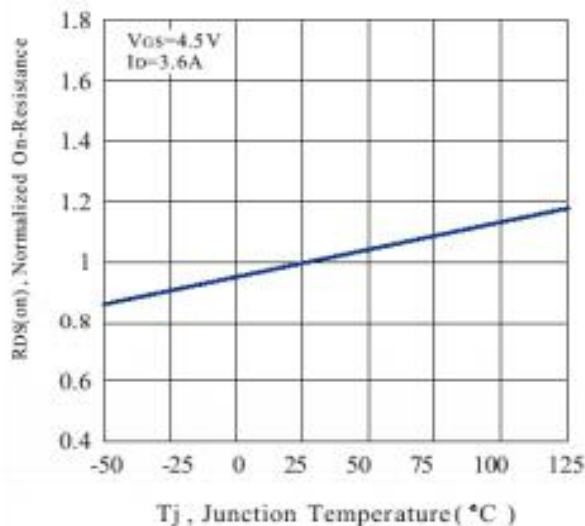


Figure 4. On-Resistance Variation with Temperature

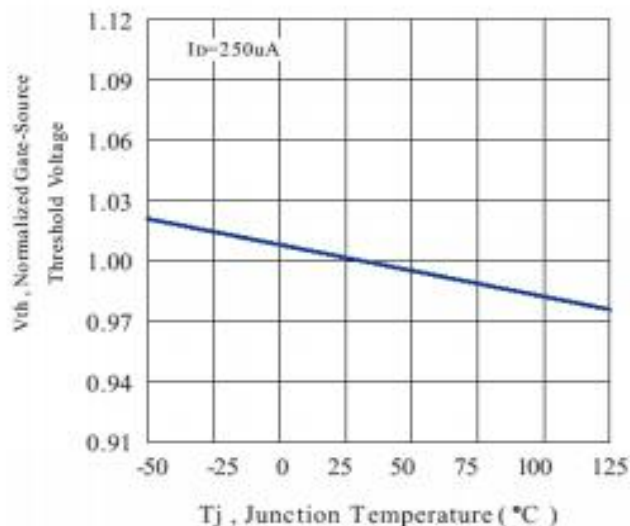


Figure 5. Gate Threshold Variation with Temperature

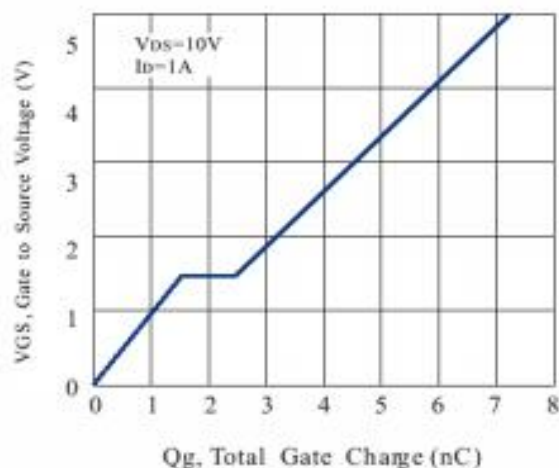


Figure 6. Gate Charge